





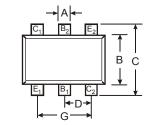
DUAL NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

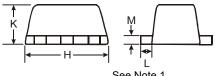
Features

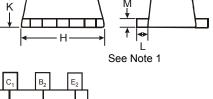
- **Epitaxial Planar Die Construction**
- Ideal for Low Power Amplification and Switching
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 3)
- "Green" Device (Note 4 and 5)

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Terminals: Lead bearing terminal plating available. See Ordering information Page 3
- Marking Information: KAP, See Page 3
- Ordering Information: See Page 3
- Weight: 0.003 grams (approximate)







SOT-563									
Dim	Min	Max	Тур						
Α	0.15	0.30	0.25						
В	1.10	1.20							
С	1.55 1.70 1.60								
D	0.50								
G	0.90 1.10		1.00						
Н	1.50	1.50 1.70							
K	0.56	0.60	0.60						
L	0.10	0.30	0.20						
M	0.10	0.18	0.11						
All Dimensions in mm									

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit	
Collector-Base Voltage	V _{CBO}	60	V	
Collector-Emitter Voltage	V _{CEO}	40	V	
Emitter-Base Voltage	V _{EBO}	6.0	V	
Collector Current - Continuous	Ic	200	mA	
Power Dissipation (Note 2)	Pd	200	mW	
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	625	°C/W	
Operating and Storage Temperature Range	T _j , T _{STG}	-55 to +150	°C	

Notes:

- 1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).
- Package is not-polarized. Parts thay be off-teet in orientation misstation, for foliated, it misstation.
 Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 3. No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

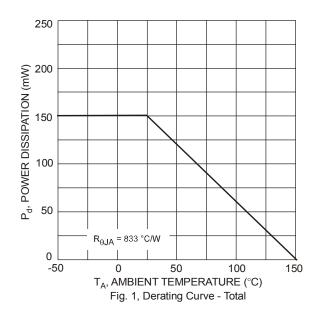
 Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

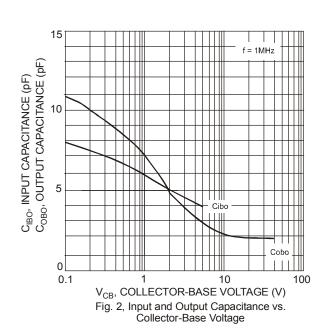


Electrical Characteristics @TA = 25°C unless otherwise specified

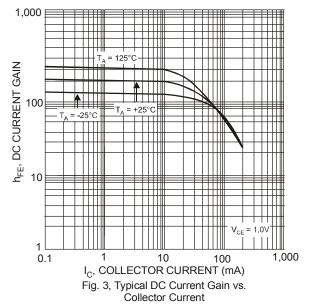
Characteristic	Symbol	Min	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 6)	•	•	•	•			
Collector-Base Breakdown Voltage	V _{(BR)CBO}	60	_	V	$I_C = 10\mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	40	_	V	$I_C = 1.0 \text{mA}, I_B = 0$		
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5.0	_	V	$I_E = 10\mu A, I_C = 0$		
Collector Cutoff Current	I _{CEX}	_	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V		
Base Cutoff Current	I _{BL}	_	50	nA	V _{CE} = 30V, V _{EB(OFF)} = 3.0V		
ON CHARACTERISTICS (Note 6)					•		
DC Current Gain	h _{FE}	40 70 100 60 30	 300 	_	$I_C = 100\mu A, V_{CE} = 1.0V$ $I_C = 1.0mA, V_{CE} = 1.0V$ $I_C = 10mA, V_{CE} = 1.0V$ $I_C = 50mA, V_{CE} = 1.0V$ $I_C = 100mA, V_{CE} = 1.0V$		
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.20 0.30	V	$I_C = 10mA$, $I_B = 1.0mA$ $I_C = 50mA$, $I_B = 5.0mA$		
Base-Emitter Saturation Voltage	V _{BE(SAT)}	0.65 —	0.85 0.95	V	I _C = 10mA, I _B = 1.0mA I _C = 50mA, I _B = 5.0mA		
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C_{obo}	_	4.0	pF	$V_{CB} = 5.0V$, $f = 1.0MHz$, $I_E = 0$		
Input Capacitance	C _{ibo}	_	8.0	pF	$V_{EB} = 0.5V$, $f = 1.0MHz$, $I_C = 0$		
Input Impedance	h _{ie}	1.0	10	kΩ			
Voltage Feedback Ratio	h _{re}	0.5	8.0	x 10 ⁻⁴	$V_{CE} = 10V, I_{C} = 1.0mA,$		
Small Signal Current Gain	h _{fe}	100	400	_	f = 1.0kHz		
Output Admittance	h _{oe}	1.0	40	μS			
Current Gain-Bandwidth Product	f _T	300	_	MHz	V _{CE} = 20V, I _C = 10mA, f = 100MHz		
Noise Figure	NF	_	5.0	dB	V_{CE} = 5.0V, I_{C} = 100 μ A, R_{S} = 1.0k Ω , f = 1.0kHz		
SWITCHING CHARACTERISTICS	•						
Delay Time	t _d	_	35	ns	$V_{CC} = 3.0V, I_C = 10mA,$		
Rise Time	t _r	_	35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$		
Storage Time	t _s		200	ns	V _{CC} = 3.0V, I _C = 10mA,		
Fall Time	t _f	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$		

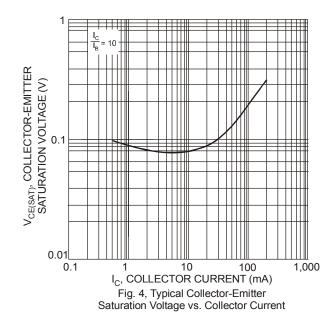
Notes: 6. Short duration pulse test used to minimize self-heating effect.

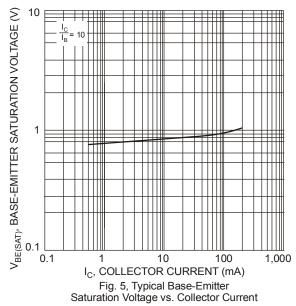










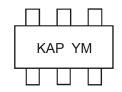


Ordering Information (Note 7)

Device	Packaging	Shipping			
MMDT3904V-7	SOT-563	3000/Tape & Reel			

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



KAP = Product Type Marking Code YM = Date Code Marking Y = Year (ex: R = 2004) M = Month (ex: 9 = September)

Date Code Key

Year	2004 2005		05	2006	2007	20	80	2009	2010	20	11	2012
Code	R		6	Т	U	\	/	W	Х	`	Y	Z
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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